7th IEEE Electron Devices Technology and Manufacturing (EDTM) Conference 2023

March 7 – 10, 2023 / COEX Seoul, Korea

26F. Oxide-Channel Ferroelectric Memories	
Session Date:	March 8(Wed.), 2023
Session Time:	17:00-18:15
Session Room:	Room F (#317)
Session Chair	Prof. Jiyong Woo (Kyungpook National University)

[26F-1] **17:00-17:15**

3D NAND Memory Operation of Oxide-Semiconductor Channel FeFETs and the Potential Impact of In-Plane Polarization

Junxiang Hao, Xiaoran Mei, Takuya Saraya, Toshiro Hiramoto and Masaharu Kobayashi

The University of Tokyo

[26F-2] **17:15-17:30**

Guideline of Device Optimization for Ferroelectric InGaZnO Transistor

Yu-Hao Chen, I-Ting Wang, Yue-Min Zheng and Tuo-Hung Hou

National Yang Ming Chiao Tung University

[26F-3] **17:30-17:45**

Back-End-of-Line-Compatible Anneal-Free Ferroelectric Field-Effect Transistor

Shih-Hao Tsai[1], Zhonghua Li[1], Ma Mo Mo Ei Phyu[1], Zihang Fang[1], Sonu Hooda[1], Chun-Kuei Chen[1], Evgeny Zamburg[1,2] and Aaron Voon-Yew Thean[1,2]

[1]National University of Singapore, [2]Singapore Hybrid-Integrated Next-Generation µ-Electronics Centre

[26F-4] **17:45-18:00**

High-Endurance (>10^{11}cycles) and Thermally-Stable Sub-100nm TiO_2 Channel FeFET for Low-Power Memory Centric 3D-LSI Applications

Taro Shiokawa, Reika Ichihara, Takamasa Hamai, Kiwamu Sakuma, Kota Takahashi, Kazuhiro Matsuo and Masumi Saitoh

Kioxia Corporation

[26F-5] **18:00-18:15**

Charge-Storage-Based vs. Non-Charge-Storage-Based 1T Non-Volatile Memory through the Interaction between Oxide Semiconductor Channel and Gate Oxide Layer

Jimin Han, Boyoung Jeong, Taeyun Noh and Tae-Sik Yoon

Ulsan National Institute of Science and Technology